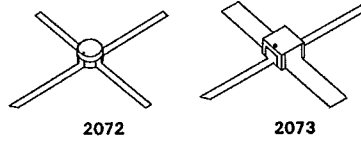


**2SK1240-1243  
(HEMT Series)**



N-Channel AlGaAs/GaAs  
Hetero Junction FET

T-31-25

**X-Band Very Low-Noise  
Amp Applications**

©3186

**Features**

- Very low noise
- High associated gain
- Our proprietary technology for forming stress-free SiNx protection film can provide the same high reliability as for MES FETs currently in use.
- AlGaAs/GaAs hetero junction

TENTATIVE



( ) : 2SK1241, 2SK1243

**Absolute Maximum Ratings at Ta = 25°C**

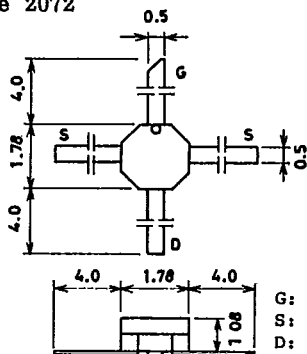
		unit
Drain to Source Voltage	V <sub>DS</sub>	4 V
Gate to Source Voltage	V <sub>GS</sub>	-3 V
Drain Current	I <sub>D</sub>	60 mA
Gate Current	I <sub>G</sub>	10 μA
Allowable Power Dissipation	P <sub>D</sub>	180 mW
Junction Temperature	T <sub>j</sub>	150 °C
Storage Temperature	T <sub>stg</sub>	-65 to +150 °C

**Electrical Characteristics at Ta = 25°C**

		min	typ	max	unit
Gate to Drain Breakdown Voltage	V <sub>(BR)GDS</sub> I <sub>G</sub> = -10μA, V <sub>DS</sub> = 0V	-3			V
Gate Cutoff Current	I <sub>GSS</sub> V <sub>GS</sub> = -3V, V <sub>DS</sub> = 0V			-10	μA
Gate to Source Cutoff Voltage	V <sub>GS(off)</sub> V <sub>DS</sub> = 2V, I <sub>D</sub> = 100μA	-0.5		-2.5	V
Drain Current	I <sub>DSS</sub> V <sub>DS</sub> = 2V, V <sub>GS</sub> = 0V	10	30	60	mA
Forward Transfer Admittance	y <sub>fs</sub>   V <sub>DS</sub> = 2V, I <sub>D</sub> = 10mA	30	40		mS
Noise Figure	NF V <sub>DS</sub> = 2V, I <sub>D</sub> = 10mA, f = 12GHz			(1.2)1.4	dB
Associated Gain	Ga V <sub>DS</sub> = 2V, I <sub>D</sub> = 10mA, f = 12GHz	9.0			dB

25K1240, 25K1241

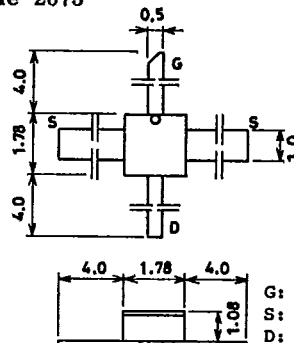
Case Outline 2072  
(unit : mm)



G: Gate  
S: Source  
D: Drain

25K1242, 25K1243

Case Outline 2073  
(unit : mm)

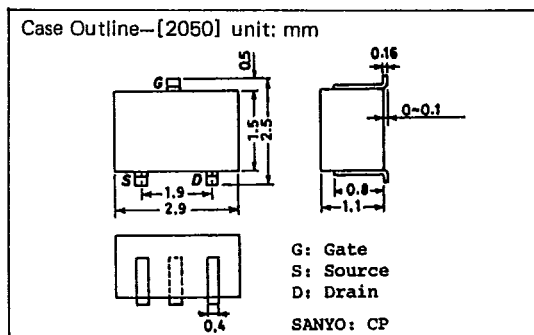
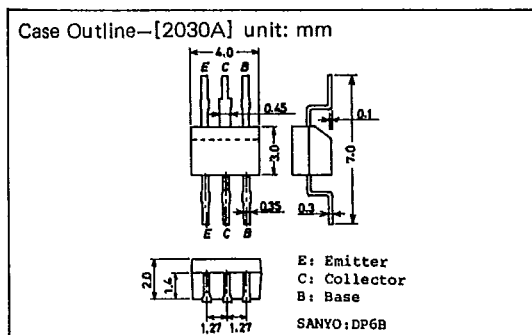
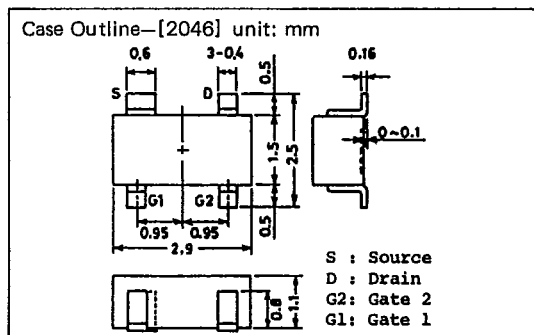
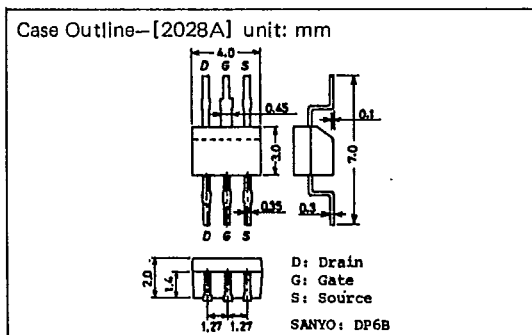
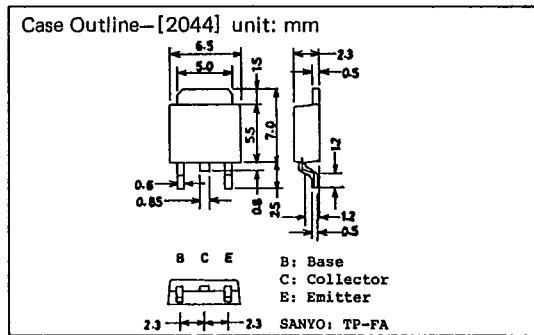
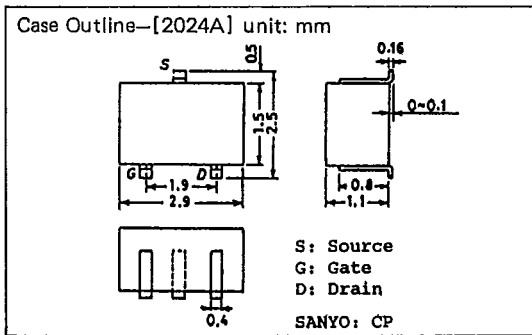
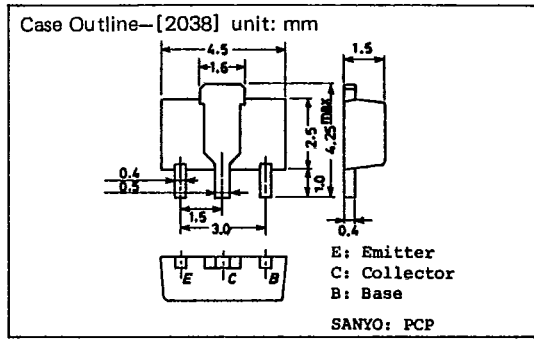
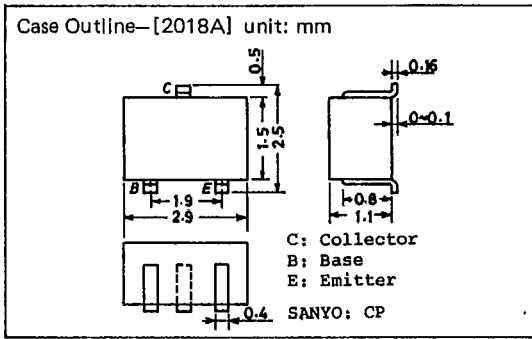


G: Gate  
S: Source  
D: Drain

T-91-20

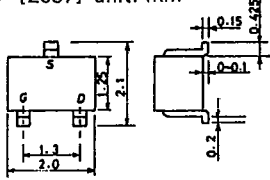
# CASE OUTLINES OF SURFACE MOUNT TRANSISTORS

- All of Sanyo surface mount transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.



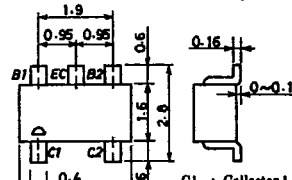
T-91-20

Case Outline—[2057] unit: mm



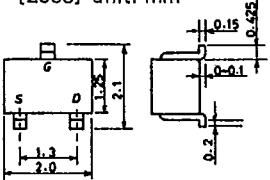
S: Source  
G: Gate  
D: Drain  
SANYO: MCP

Case Outline—[2066] unit: mm



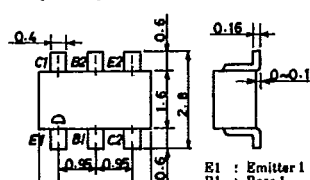
C1 : Collector 1  
C2 : Collector 2  
B2 : Base 2  
EC : Emitter Common  
B1 : Base 1  
SANYO : CP6

Case Outline—[2058] unit: mm



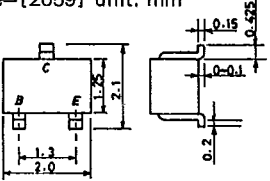
G: Gate  
S: Source  
D: Drain  
SANYO: MCP

Case Outline—[2067] unit: mm



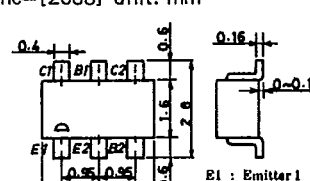
E1 : Emitter 1  
B1 : Base 1  
C2 : Collector 2  
E2 : Emitter 2  
B2 : Base 2  
C1 : Collector 1  
SANYO : CP6

Case Outline—[2059] unit: mm



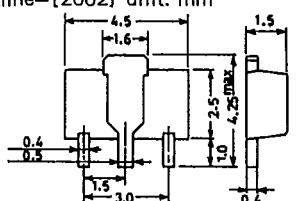
B: Base  
C: Collector  
E: Emitter  
SANYO: MCP

Case Outline—[2068] unit: mm



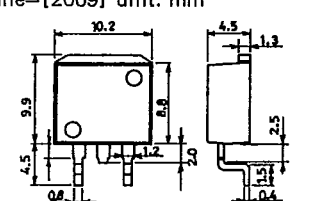
B1 : Emitter 1  
E2 : Emitter 2  
B2 : Base 2  
C2 : Collector 2  
B1 : Base 1  
C1 : Collector 1  
SANYO : CP6

Case Outline—[2062] unit: mm



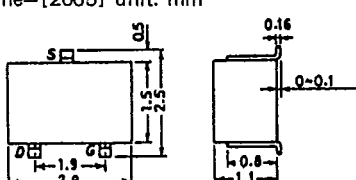
S: Source  
D: Drain  
G: Gate  
SANYO: PCP

Case Outline—[2069] unit: mm



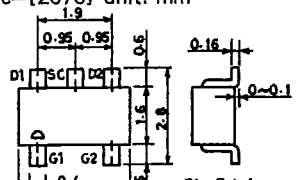
B: Base  
C: Collector  
E: Emitter  
SANYO: SMP

Case Outline—[2065] unit: mm



S: Source  
D: Drain  
G: Gate  
SANYO: CP

Case Outline—[2070] unit: mm



G1 : Gate 1  
G2 : Gate 2  
D2 : Drain 2  
SC : Source Common  
D1 : Drain 1  
SANYO : CP6

T-9120

